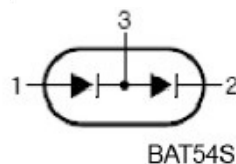
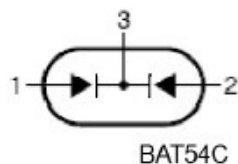
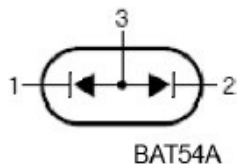
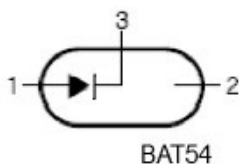
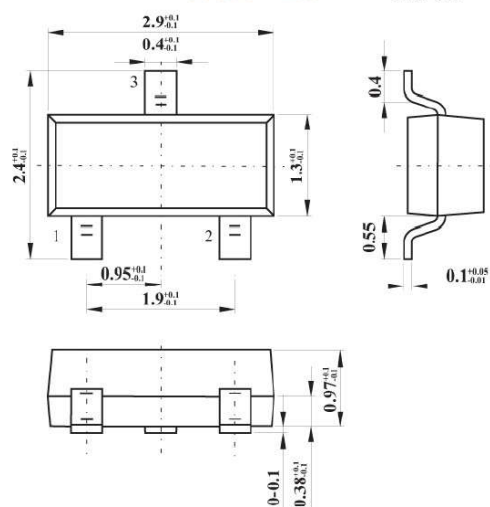


Schottky Diodes

■ Features

- Low forward voltage
- Guard ring protected
- Small plastic SMD package.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Maximum Repetitive Reverse Voltage	V_{RRM}	30	V
Average Rectified Forward Current	$I_F(AV)$	200	mA
Non-repetitive Peak Forward Surge Current Pulse width = 1.0 second	I_{FSM}	600	mA
Power Dissipation	P_D	290	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	430	$^\circ\text{C}/\text{W}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature	T_J	150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Breakdown Voltage	V_R	$I_R = 10 \mu\text{A}$	30			V
Forward Voltage	V_F	$I_F = 0.1 \text{ mA}$			240	mV
		$I_F = 1 \text{ mA}$			320	mV
		$I_F = 10 \text{ mA}$			400	mV
		$I_F = 30 \text{ mA}$			500	mV
		$I_F = 100 \text{ mA}$			1.0	V
Reverse Current	I_R	$V_R = 25 \text{ V}$			2	μA
Total Capacitance	C_T	$V_R = 1 \text{ V}, f = 1.0 \text{ MHz}$			10	pF
Reverse Recovery Time	t_{rr}	$I_F = I_R = 10 \text{ mA}, I_{RR} = 1.0 \text{ mA}, R_L = 100\Omega$			5	ns

SHIKE MAKE CONSCIOUS PRODUCT

CONSCIOUS PRODUCTS BEGIN WITH CONSCIOUS PEOPLE



■ Typical Characteristics

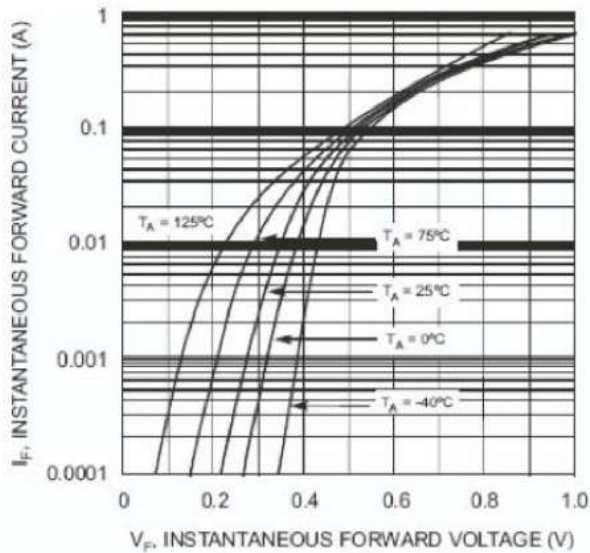


Fig.1 Forward Characteristics

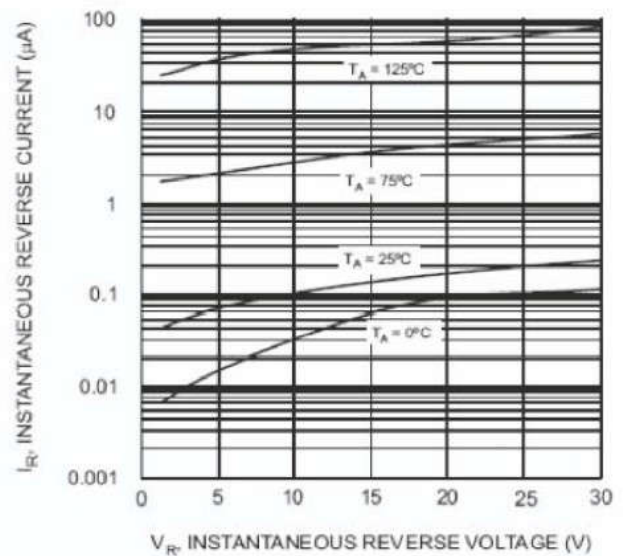


Fig.2 Typical Reverse Characteristics

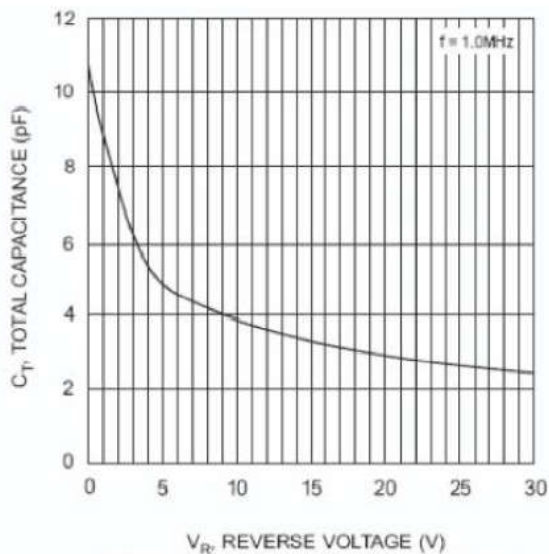


Fig.3 Typical Capacitance vs. Reverse Voltage

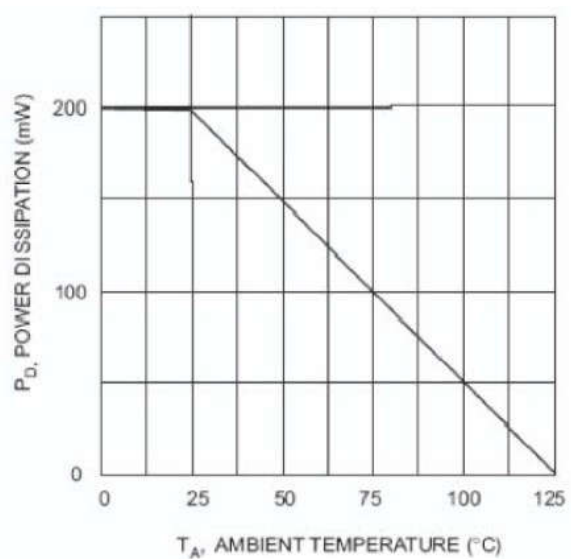


Fig.4 Power Derating Curve

